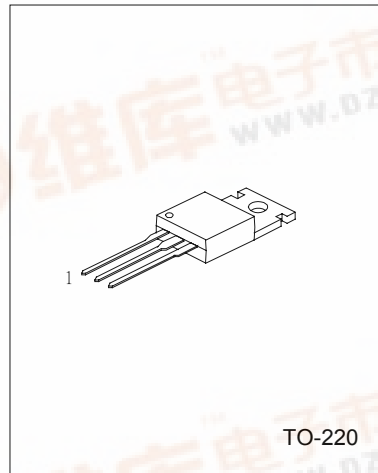


UTC2SB834 PNP EPITAXIAL SILICON TRANSISTOR

HIGH VOLTAGE TRANSISTOR

DESCRIPTION

Low frequency power amplifier applications.



TO-220

1:BASE 2: COLLECTOR 3: EMITTER

ABSOLUTE MAXIMUM RATINGS (Operating temperature range applies unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	60	V
Collector-emitter voltage	V _{CEO}	60	V
Emitter-base voltage	V _{EB0}	7	V
Total Power Dissipation(T _a =25°C)	P _c	30	W
Collector current	I _c	3	A
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C
Base Current	I _B	0.5	A

ELECTRICAL CHARACTERISTICS(T_a=25°C,unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	BV _{CEO}	I _c =50mA	60			V
Collector cut-off current	I _{cBO}	V _{CB} =60V			100	μA
Emitter cut-off current	I _{eBO}	V _{EB} =7V			100	μA
Collector-emitter saturation voltage	V _{CE(SAT)}	I _c =3A, I _B =0.3A			1	V
Collector-emitter on voltage	V _{CE(ON)}	V _{CE} =5V, I _c =0.5A		0.7	1	V
DC current gain	h _{FE1}	I _c =0.5A, V _{CE} =5V	60		300	
	h _{FE2}	I _c =3A, V _{CE} =5V	20			
Current gain bandwidth product	f _T	V _{CE} =5V, I _c =0.5A		9		MHZ

CLASSIFICATION of h_{FE1}

RANK	O	Y	GR
RANGE	60-120	100-200	150-300

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1

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